

性能特点：

- 频率范围：DC-67GHz
- 衰减范围：1/2/3/4/5/6/7/8/9/10dB
- 插损波动：0.6dB
- 输入/输出电压驻波比：1.5/1.5
- 芯片尺寸：0.60mm×0.60mm×0.1mm

产品简介：

HH-AT67 是一款性能优良的 GaAs MMIC 固定衰减器，该芯片通过背面金属经通孔接地。芯片覆盖 DC-67GHz 频带范围，衰减范围可选，插损波动小于 0.6dB，输入输出电压驻波比小于 1.5。

电参数：(TA=25°C)

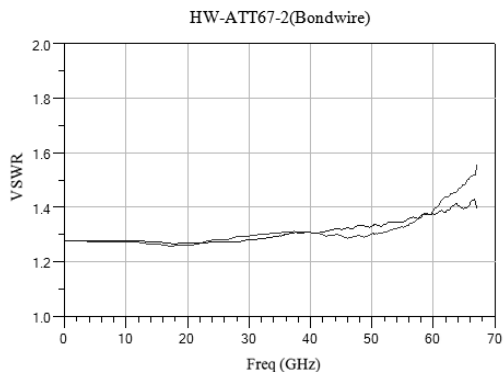
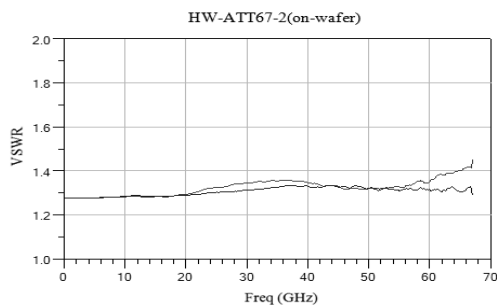
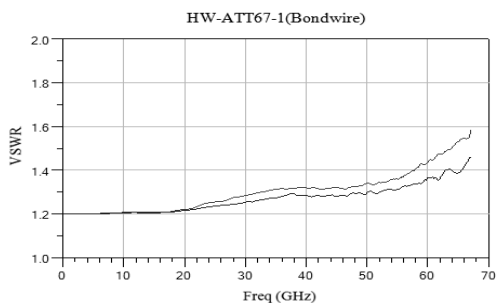
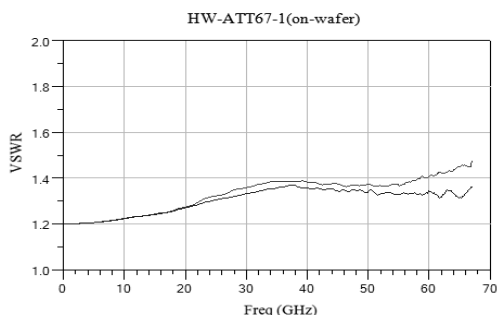
指标		最小值	典型值	最大值	单位
频率范围		DC-67			GHz
衰减量	1dB	0.9	1	1.8	dB
	2dB	1.9	2	2.5	dB
	3dB	3	3	3.7	dB
	4dB	4	4	4.5	dB
	5dB	5	5	5.3	dB
	6dB	6	6	6.4	dB
	7dB	7	7	7.2	dB
	8dB	8	8	8.5	dB
	9dB	9	9	9.5	dB
	10dB	10	10	10.3	dB
输入驻波比		-	1.4	1.5	-
输出驻波比		-	1.4	1.5	-

使用限制参数：(超过以上任何一项最大限额都有可能造成永久损坏。)

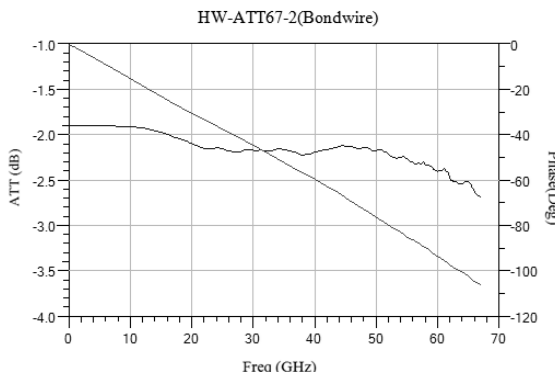
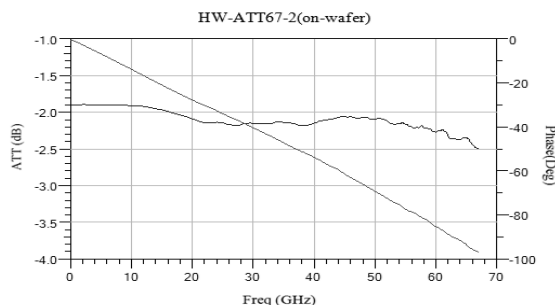
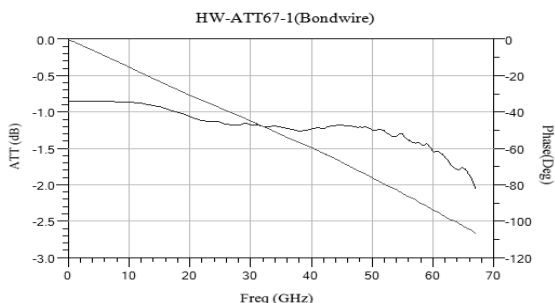
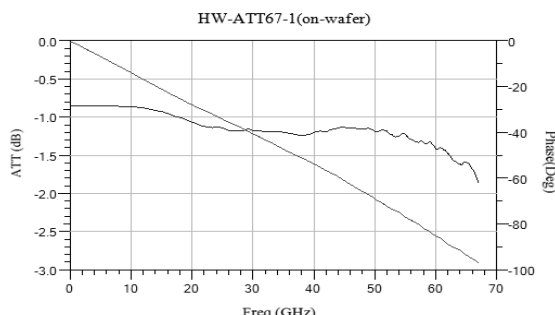
最大输入功率	27 dBm
存储温度	-65°C-150°C
使用温度	-55°C-125°C

典型曲线：

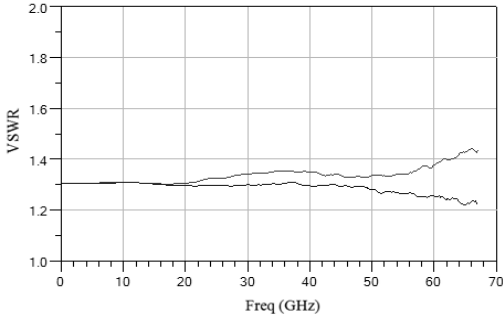
输入输出驻波比



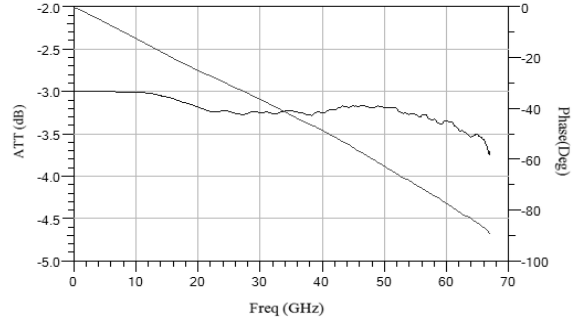
插损



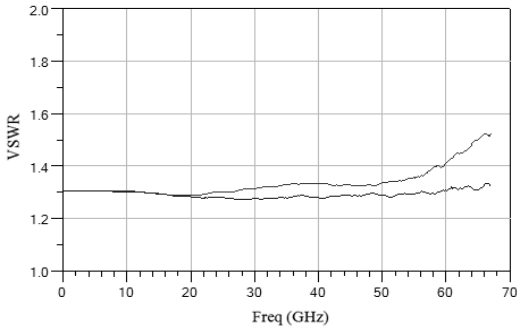
HW-ATT67-3(on-wafer)



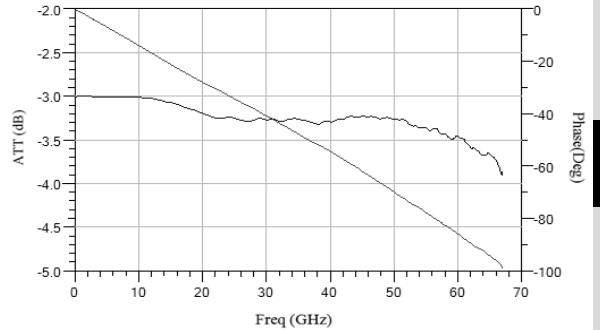
HW-ATT67-3(on-wafer)



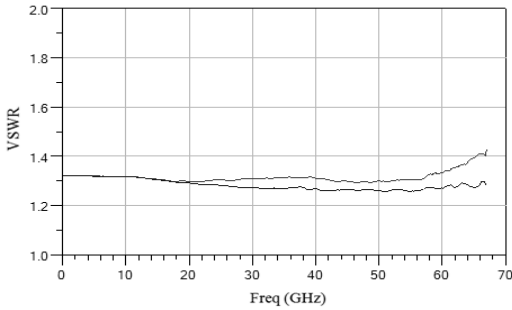
HW-ATT67-3(Bondwire)



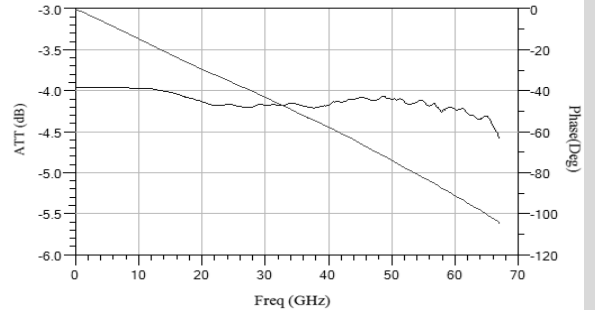
HW-ATT67-3(Bondwire)



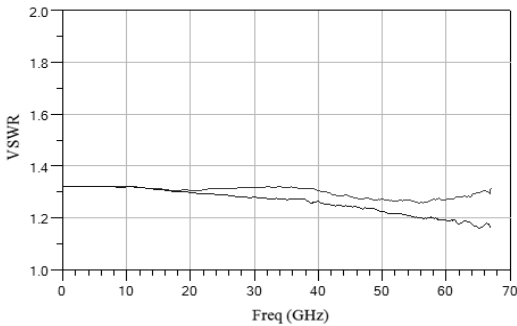
HW-ATT67-4(Bondwire)



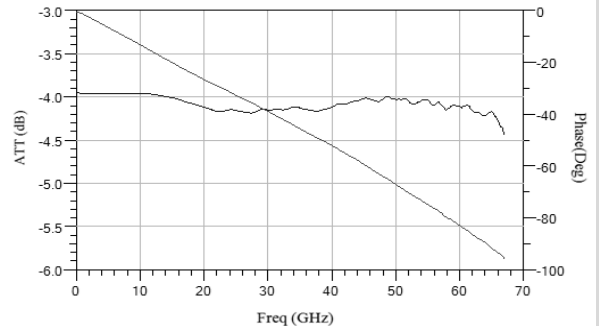
HW-ATT67-4(Bondwire)



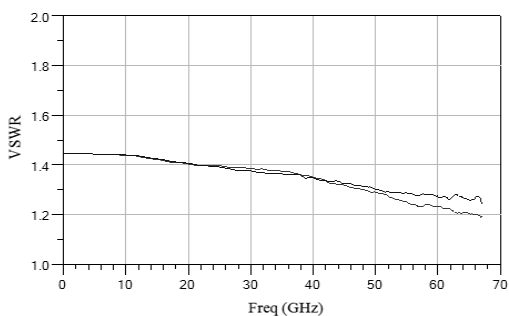
HW-ATT67-4(on-wafer)



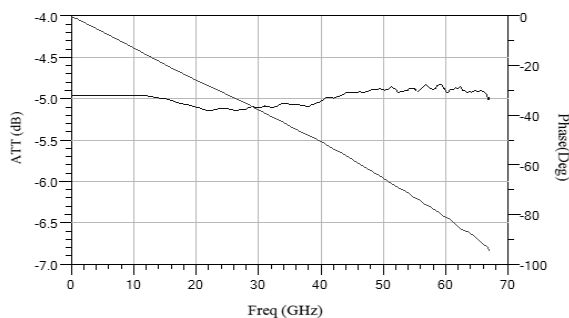
HW-ATT67-4(on-wafer)



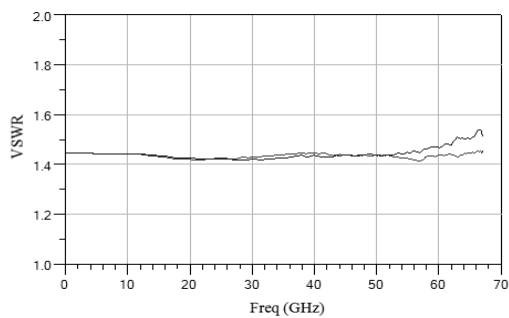
HW-ATT67-5(on-wafer)



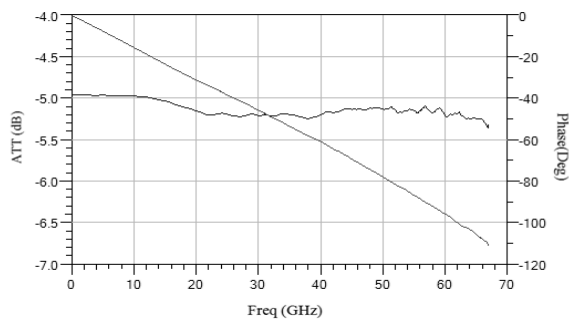
HW-ATT67-5(on-wafer)



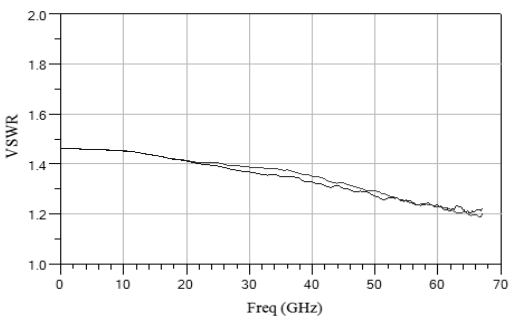
HW-ATT67-5(Bondwire)



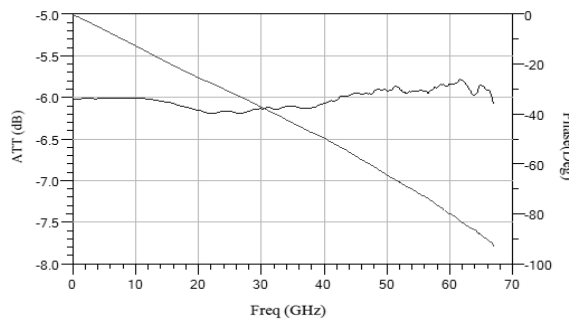
HW-ATT67-5(Bondwire)



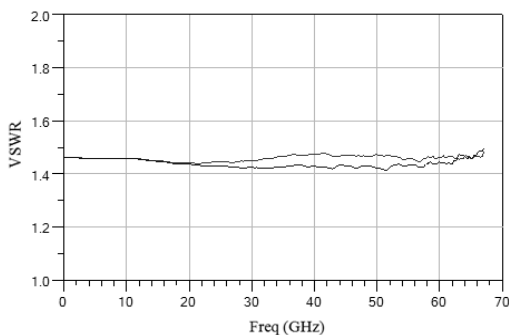
HW-ATT67-6(on-wafer)



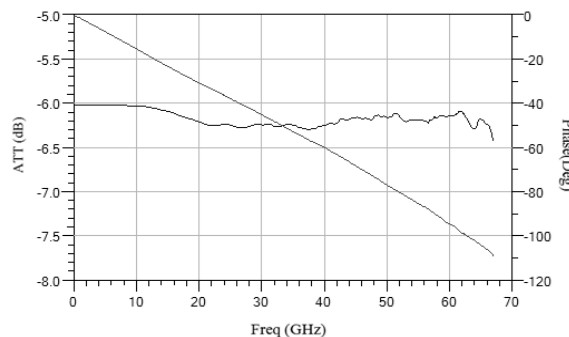
HW-ATT67-6(on-wafer)



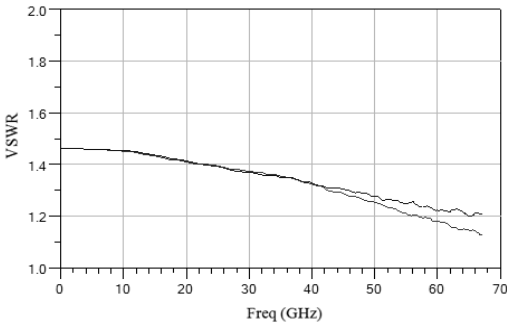
HW-ATT67-6(Bondwire)



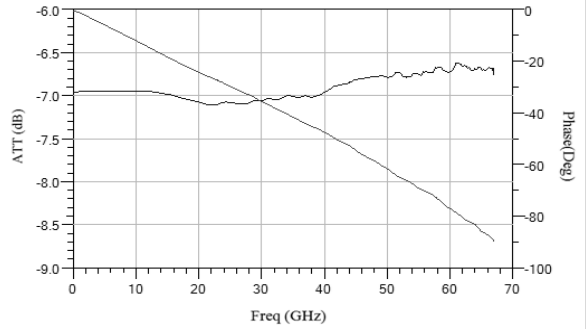
HW-ATT67-6(Bondwire)



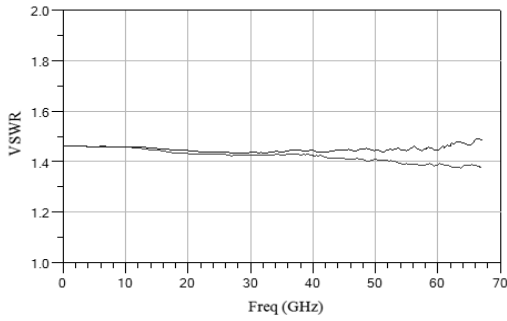
HW-ATT67-7(on-wafer)



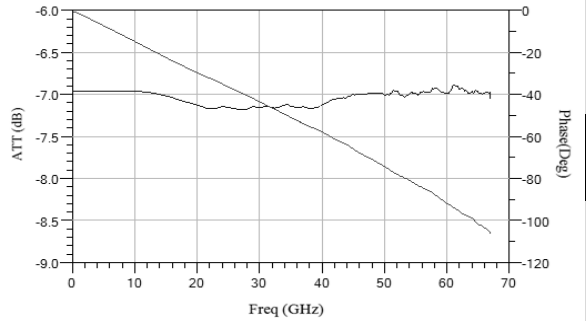
HW-ATT67-7(on-wafer)



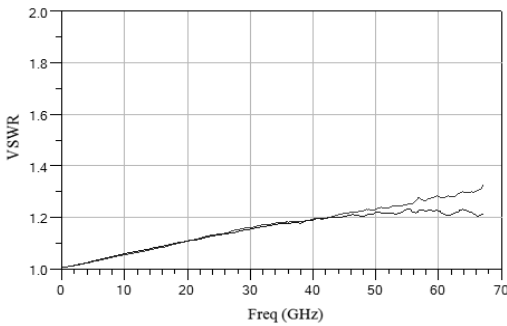
HW-ATT67-7(Bondwire)



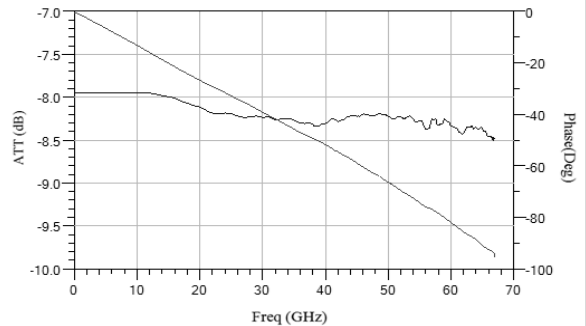
HW-ATT67-7(Bondwire)



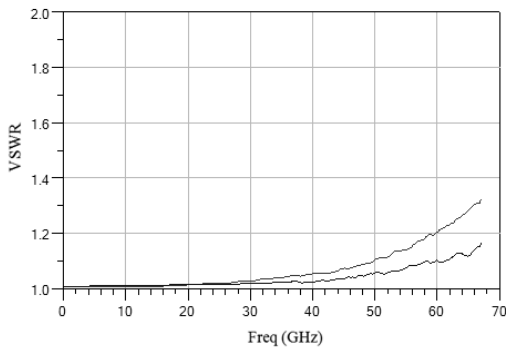
HW-ATT67-8(on-wafer)



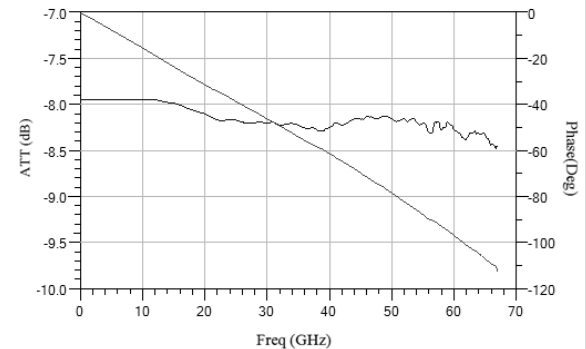
HW-ATT67-8(on-wafer)



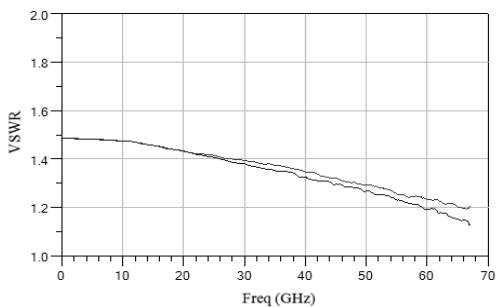
HW-ATT67-8(Bondwire)



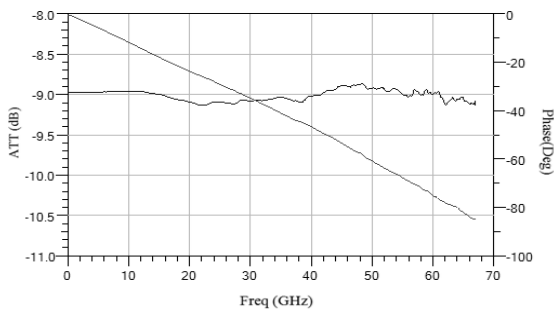
HW-ATT67-8(Bondwire)



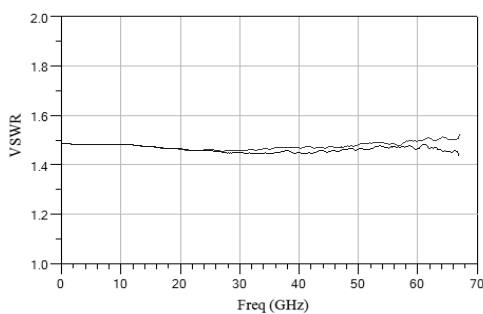
HW-ATT67-9(on-wafer)



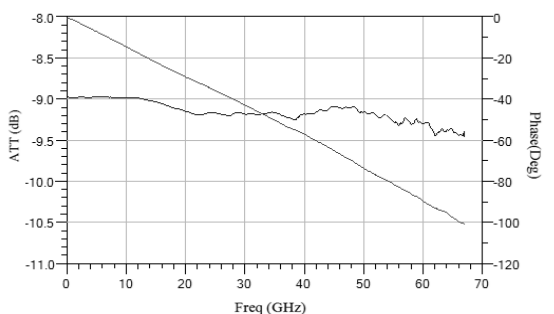
HW-ATT67-9(on-wafer)



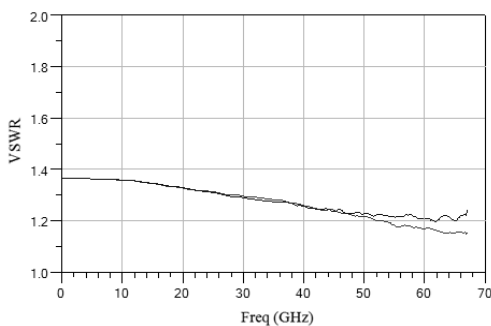
HW-ATT67-9(Bondwire)



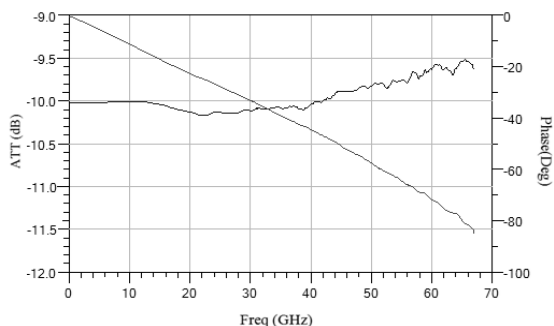
HW-ATT67-9(Bondwire)



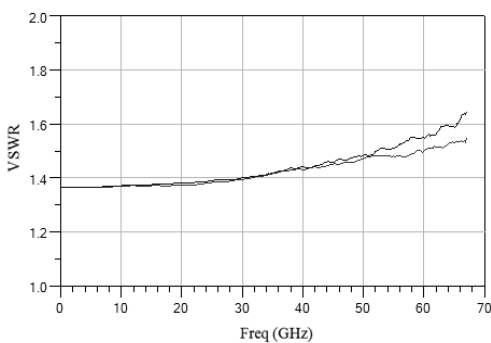
HW-ATT67-10(on-wafer)



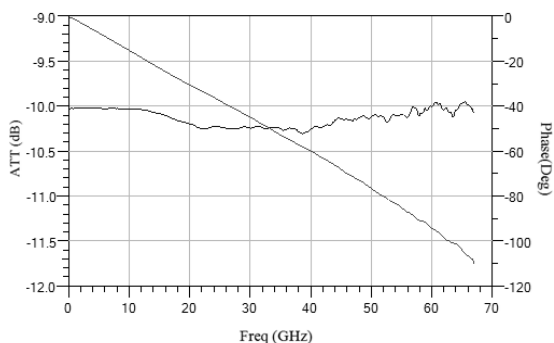
HW-ATT67-10(on-wafer)



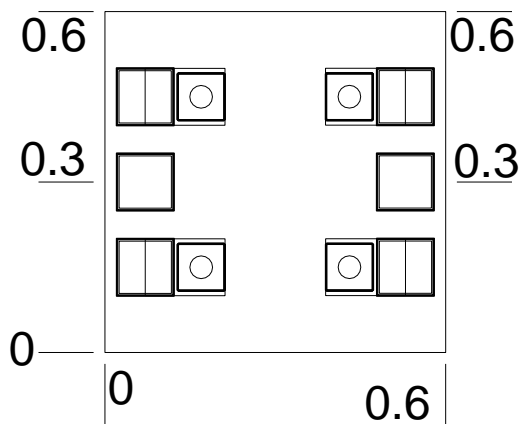
HW-ATT67-10(Bondwire)



HW-ATT67-10(Bondwire)

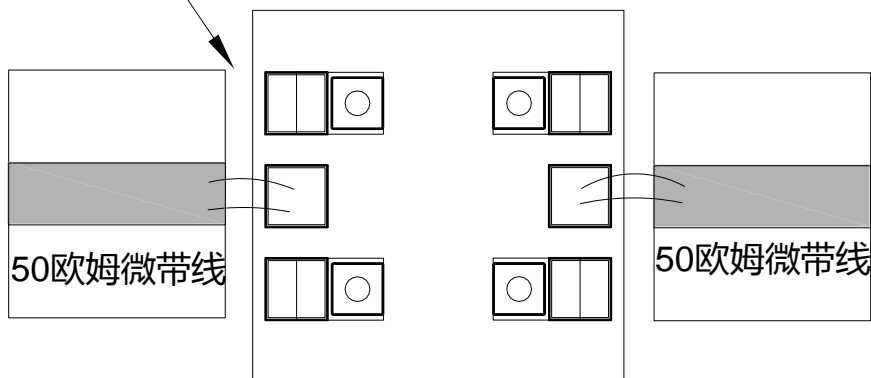


尺寸图：(单位 mm)



建议装配图：

3mil典型缝隙



使用说明：

存储：芯片必须放置于具有静电防护功能的容器中，并在氮气环境下保存。

清洁处理：裸芯片必须在净化环境中操作使用，禁止采用液态清洁剂对芯片进行清洁处理。

静电防护：请严格遵守 ESD 防护要求，避免器件静电损伤。

常规操作：拿取芯片请使用真空夹头或精密尖头镊子。操作过程中要避免工具或手指触碰到芯片表面。

装架操作：芯片安装可采用 AuSn 焊料共晶焊接或导电胶粘接工艺。安装面必须清洁平整。

键合操作：输入输出各用 2 根（建议直径 25um 金丝）键合线，键合线长度小于 250um 最优。建议采用尽可能小的超声波能量。键合时起始于芯片上的压点，终止于封装（或基板）。